MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

DRV8837DSGR-MS

Product specification





GENERAL DESCRIPTION

DRV8837DSGR-MS are low voltage DC IC.motor driver Internal integration 650mΩ(HS+LS typical) H bridge N MOS switch, whichcan support the 1.8V~11V input voltage range. The Peak current capacity is up to1.5A, support for ultra-low power sleep mode; built-inUVLO, Thermal Shutdown, OCP protection circuit. DRV8837DSGR-MS can be used in camera, toys and consumer products.

FEATURES

- Support the input voltage range:
 Motor power: 1.8V~11V
 - Control power supply: 1.8V~7V
- LDMOS R_{DS(ON)} (HS+LS) 650mΩ (typical)
- Ultra-low power sleep mode
- 45nA (typical) VM sleep mode current
- 17nA (typical) VCC sleep mode current
- Up to 1.5A Peak current output capacity

- Built-in UVLO Protection
- Built-in Over Temperature Protection
- Built-in Short Circuit Protection
- Built-in Over Current Protection
- Built-in Charge Pump
- WSON-8-EP(2*2) package

APPLICATION

- Cameras
- Toys
- Consumer Products

Reference News

WSON-8-EP(2*2)	Pin Configuration	MARKING
CCC COMPANY OF THE PARK OF THE	VM 1 8 VCC OUT1 2 7 EN Exposed Pad 6 IN1 GND 4 5 IN2	TFC* **

Order information

P/N	PKG	QTY	
DRV8837DSGR-MS	WSON-8-EP(2*2)	3000PCS	



PIN FUNCTIONS

Pin	Name	Function
1	VM	Power Supply for Driver. Connect a 0.1 µF bypass ceramic capacitor to GND. A bulk capacitor with at least 22 µF capacitance on VM to GND is needed and helpful to stabilize VM voltage during motor operation.
2	OUT1	Motor Driver output 1
3	OUT2	Motor Driver output 2
4	GND	Ground pin
5	IN2	PWM input2
6	IN1	PWM input1
7	EN	Chip Enable Input Pin. When this pin is in logic low, the device enters low-power sleep mode. The device operates normally when this pin is logic high. The pin has an internal pull-down resistor to GND.
8	VCC	Power Supply for Logic Input. Connect a 0.1µF bypass ceramic capacitor to GND

YPICAL APPILCATION

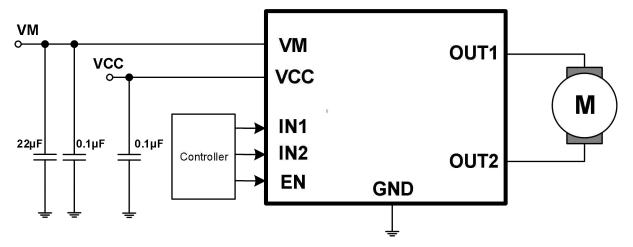


Figure 1. Basic Application Circuit



ABSOLUTE MAXIMUM RATINGS

Parameter	Value	Unit
VM Voltage Range	-0.3~11	V
VCC, IN1, IN2, EN Voltages Range	-0.3~7	V
OUT1, OUT2 Voltage Range	-0.3~Vin+0.3	V
Storage Temperature Range	-50~150	°C
Junction Temperature	-40~150	°C
Package Thermal Resistance θ _{JA} of DFN2x2-8	70	°C/W
Package Thermal Resistance θ _{JA} of SOP8	90	°C/W

ESD RATING

Items	Description	Value	Unit
Vesd	Human Body Model for all pins	±2000	V

JEDEC specification JS-001

RECOMMENDED OPERATING CONDITIONS

Itms	Descriptione Min Max			Unit
Voltage Range	VM	1.8	11	V
TJ	Operating Junction Temperature Range	-40	125	°C



ELECTRICAL CHARACTERISTICS

(V_M =5V, T_A = 25 $^{\circ}$ C, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Power Supplies (VM and V	CC)					
VM Voltage Range	VvM		1.8		11	V
VAA Committee Committee		VM=5V, VCC=3V No PWM		124		μA
VM Supply Current	I∨M	VM=5V, VCC=3V 50kHz PWM		0.53		mA
VM sleep mode supply current	IVMQ	VM=5V, VCC=3V Sleep Mode		45	95	nA
VCC Voltage Range	Vvcc		1.8		7	V
VCC Supply Current	haa	VM=5V, VCC=3V No PWM		180		μA
VCC Supply Current	lvcc	VM=5V, VCC=3V 50kHz PWM		0.32		mA
VCC sleep mode supply current	Ivccq	VM=5V, VCC=3V Sleep Mode		17	35	nA
PWM Control Logic Inputs (IN1, I	N2 and EN)		<u>.</u>	•		
Input Logic Low Voltage Falling Threshold	VIL_F		0.25x VCC	0.4x VCC		V
Input Logic High Voltage Rising Threshold	VIH_R			0.5x VCC	0.6x VCC	V
Input logic Hysteresis	VHYS			0.1x VCC		V
Input Logic Low Current	lıL		-5		5	μA
Input Logic High Current	lн				40	μA
Input Pull Down Resistor	Rın			100		kΩ
Motor Driver Outputs (OUT1 and	OUT2)					
Output Switch On-Resistance (HS+LS)	Ron			0.65		Ω
Output Switch Leakage Current	ILEAK		-200		200	nA
Protection Function	·			·		
VCC UVLO Voltage	Vuvlo			1.7		V
UVLO Hysteresis	V _{UVLO_HY}			100		mV
Over Current Protection	Іоср		1.6	1.75		Α
Over Current Retry Time	Tocp_rt			1		ms
Thermal Shutdown Threshold	Tsdn			160		°C
Thermal Shutdown Hysteresis	T _{SDN_HY}			20		°C



ELECTRICAL CHARACTERISTICS(continued) (V_{IN}=5V, T_A = 25°C, unless otherwise noted.)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output Enable time	T ₁			180	265	ns
Output Disable time	T ₂			70	100	ns
Delay Time IN1 low to OUT2 high IN2 low to OUT1 high	Т3			140	215	ns
Delay Time IN2 high to OUT1 low IN1 high to OUT2 low	T ₄			160	240	ns
Output rise time	T ₅			60	120	ns
Output fall time	T ₆			38	100	ns

FUNCTIONAL BLOCK DIAGRAM

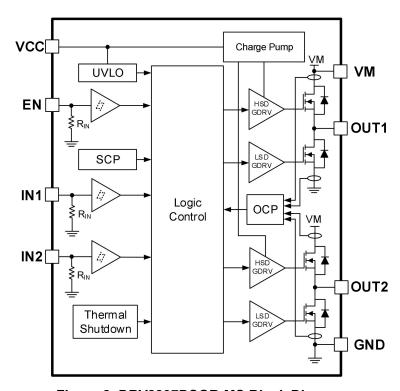
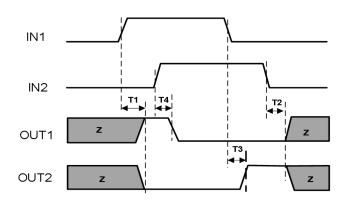
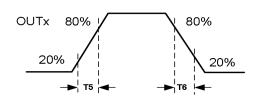


Figure 2. DRV8837DSGR-MS Block Diagram



INPUT OUTPUT LOGIC



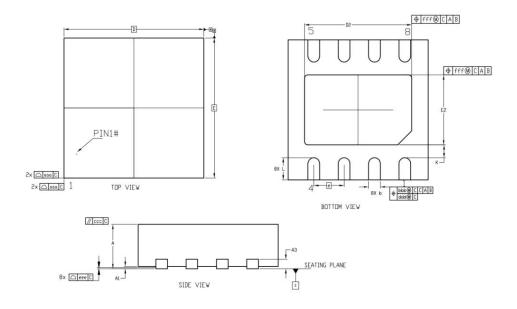


EN	IN1	IN2	OUT1	OUT2	Function
0	X	X	Z	Z	Coast
1	0	0	Z	Z	Coast
1	1	0	Н	L	Forward
1	0	1	L	Н	Reverse
1	1	1	L	L	Brake



PACKAGE INFORMATION

WSON-8-EP(2*2)



Unit: mm

Cumbal	Dimensions In Millimeters		Symbol	Dimensions In Millimeters			
Symbol	Min Typ Max	Symbol	Min	Тур	Max		
Α	0.70	0.75	0.80	L	0.30	0.35	0.40
A1	0	0.02	0.05	K	0.20	-	-
А3	-	0.20 REF	-	aaa	-	0.15	-
b	0.19	0.24	0.29	bbb	-	0.10	-
D	2.00 BSC			ccc	-	0.10	-
E	2.00 BSC		ddd	-	0.05	-	
D2	1.25	1.30	1.35	eee	-	0.08	-
E2	0.75	0.80	0.85	fff	-	0.10	-
е		0.50 BSC					

Note:

1) All dimensions are in millimeters.



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